



NTE2401 Silicon PNP Transistor RF Stages in FM Front Ends

Description:

The NTE2401 is a silicon PNP transistor in a plastic SOT-23 type surface mount package designed for use in RF stages in FM front-ends in common base configuration for SMD applications.

Absolute Maximum Ratings:

| | |
|---|----------------|
| Collector–Base Voltage, V_{CBO} | 30V |
| Collector–Emitter Voltage, V_{CEO} | 30V |
| Emitter–Base Voltage, V_{EBO} | 4V |
| DC Collector Current, I_C | 25mA |
| Total Power Dissipation ($T_A \leq +25^\circ\text{C}$, Note 1), P_{tot} | 300mW |
| Operating Junction Temperature, T_J | +150°C |
| Storage Temperature Range, T_{stg} | -55° to +150°C |
| Thermal Resistance, Junction-to-Ambient (Note 1), R_{thJA} | 430K/W |

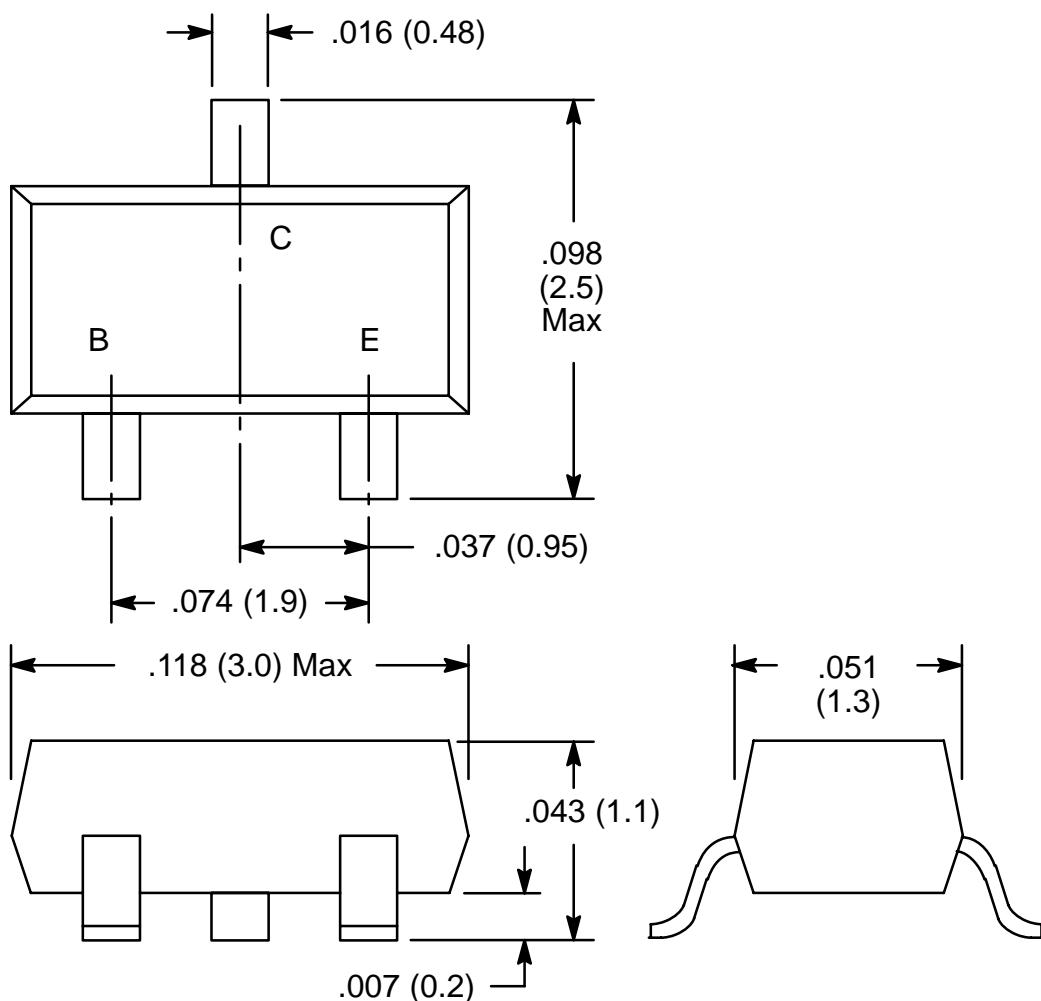
Note 1. Mounted on a ceramic substrate of .314 (8mm) x .393 (10mm) x .027 (0.7mm).

Electrical Characteristics: ($T_J = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|--------------------------|-----------|---|-----|------|-----|------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 30V$, $I_E = 0$ | — | — | 50 | nA |
| Emitters Cutoff Current | I_{EBO} | $V_{EB} = 4V$, $I_C = 0$ | — | — | 10 | μA |
| Base Current | I_B | $V_{CE} = 10V$, $I_C = 4mA$ | — | 80 | 160 | μA |
| | | $V_{CE} = 10V$, $I_C = 1mA$ | — | 22 | — | μA |
| Base–Emitter Voltage | V_{BE} | $V_{CE} = 10V$, $I_C = 4mA$ | — | 0.76 | — | V |
| Transition Frequency | f_T | $V_{CE} = 10V$, $I_C = 1mA$ | — | 350 | — | MHz |
| | | $V_{CE} = 10V$, $I_C = 4mA$ | — | 450 | — | MHz |
| | | $V_{CE} = 10V$, $I_C = 8mA$ | — | 440 | — | MHz |
| Feedback Capacitance | C_{rb} | $V_{CE} = 10V$, $V_{EB} = 0$ | — | 0.1 | — | pF |
| Noise Factor | F | $V_{CE} = 10V$, $I_C = 2mA$, $G_s = 16.7mS$ | — | 3.0 | — | dB |
| | | $V_{CE} = 10V$, $I_C = 5mA$, $G_s = 6.7mS$, $jB_s = 5mS$ | — | 3.5 | — | dB |

Electrical Characteristics (Cont'd): ($T_J = +25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|------------------------------------|----------------|---|-----|------|-----|---------------|
| y-parameters (common base) | | | | | | |
| Input Conductance | g_{ib} | $V_{CB} = 10\text{V}$, $I_C = 4\text{mA}$, $f = 100\text{MHz}$ | - | 125 | - | mS |
| Input Capacitance | C_{ib} | | - | 64 | - | pF |
| Transfer Admittance | $ y_{fb} $ | | - | 100 | - | mS |
| Phase Angle of Transfer Admittance | φ_{fb} | | - | 147 | - | $^\circ$ |
| Output Conductance | g_{ob} | | - | 40 | - | μS |
| Output Capacitance | C_{ob} | | - | 1.25 | - | pF |
| Feedback Admittance | $ y_{rb} $ | | - | 220 | - | μS |
| Phase Angle of Feedback Admittance | φ_{rb} | | - | 85 | - | $^\circ$ |



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